

## Supporting Information

### **Controlled 2D Growth Approach via Atomic Layer Deposition for Improved Stability and Performance in Flexible SnO Thin-film Transistors**

*Hye-Mi Kim<sup>a</sup>, Won-Bum Lee<sup>a</sup>, Haklim Koo<sup>b</sup>, Seo Yeong Kim<sup>b</sup>, and Jin-Seong Park<sup>a,\*</sup>*

Hye-Mi Kim, Won-Bum Lee, and Jin-Seong Park

Division of Materials Science and Engineering, Hanyang University, 222, Wangsimni-ro,  
Seongdong-gu, Seoul, 04763, Republic of Korea

Haklim Koo, Seo Yeong Kim

Department of Display Science and Engineering, Hanyang University, 222, Wangsimni-ro,  
Seongdong-gu, Seoul, 04763, Republic of Korea

E-mail: [jsparklime@hanyang.ac.kr](mailto:jsparklime@hanyang.ac.kr)

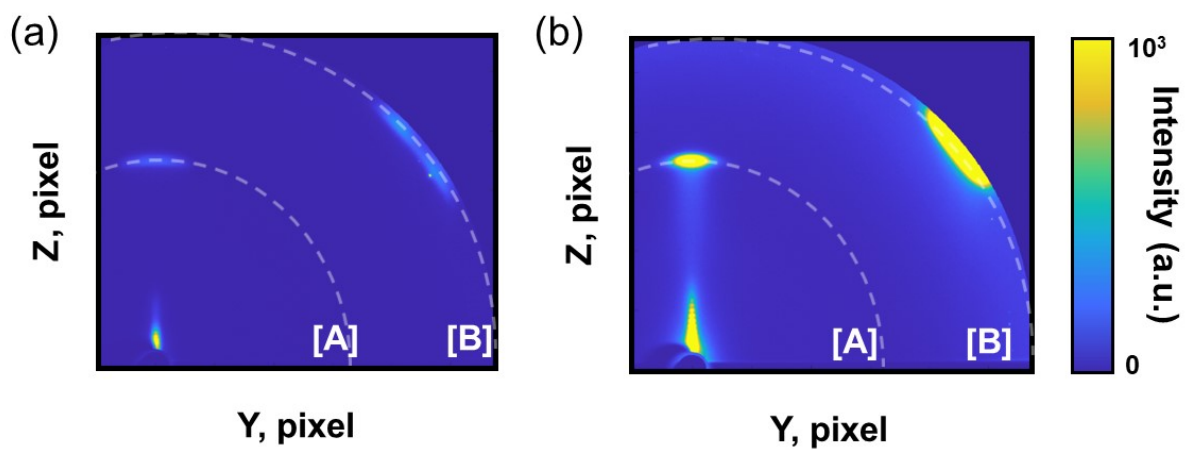


Figure S1. GIWAXS image as pixel map and color map of intensity. (a) SnO film deposited by (1s-15s) and (b) (0.3s-5s)\*3 process.

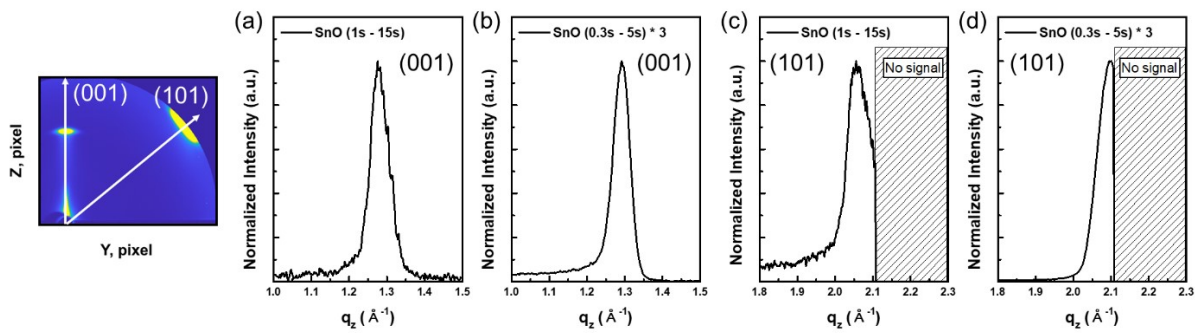


Figure S2. Linear plot ( $q_z$  versus normalized intensity) of each pixel maps in Figure S1. 90° plot of the (001) plane of (a) SnO film deposited by (1s-15s) and (b) (0.3s-5s)\*3 process and (101) plane of (c) SnO film deposited by (1s-15s) and (d) (0.3s-5s)\*3 process.

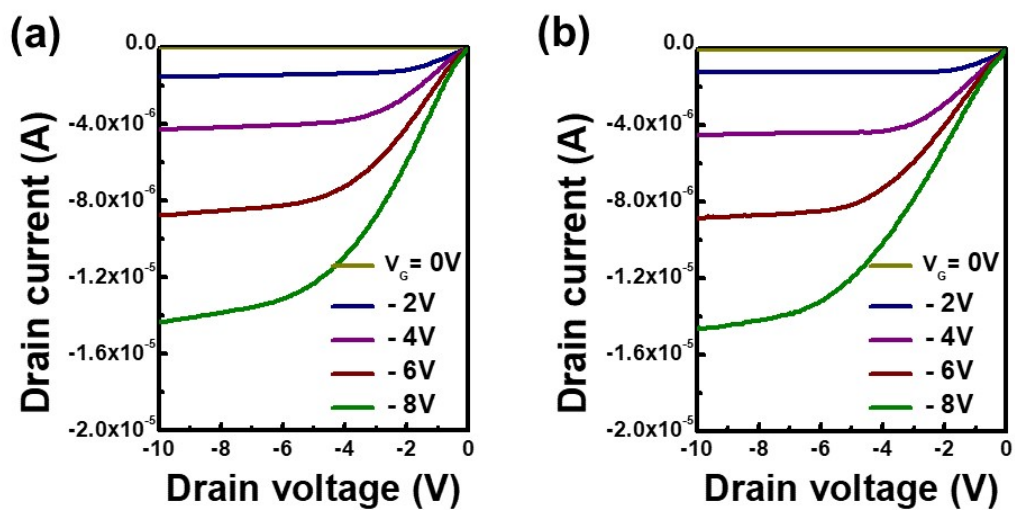


Figure S3. Output curves of SnO channel TFTs fabricated by precursor (a) ( $\times 1$ ) and (b) ( $\times 3$ ).